



**THE DATASHEET OF
MBRF20L45CTG**



MBR20L45CTG, MBRF20L45CTG

Switch-mode Power Rectifier 45 V, 20 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

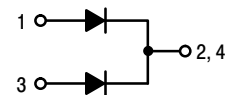
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- These Devices are Pb-Free and are RoHS Compliant*



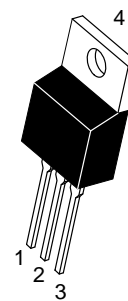
ON Semiconductor®

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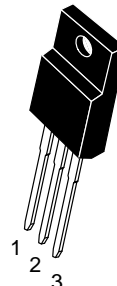
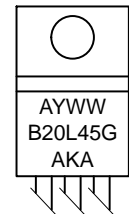
DUAL SCHOTTKY BARRIER RECTIFIERS 20 AMPERES, 45 VOLTS



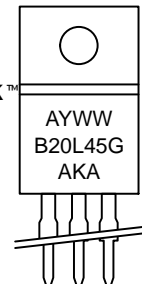
MARKING DIAGRAMS



TO-220
CASE 221A
STYLE 6



TO-220 FULLPAK™
CASE 221AH



B20L45 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping
MBR20L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF20L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R) $T_C = 141^\circ\text{C}$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz)	I_{FRM}	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	180	A
Operating Junction Temperature (Note 1)	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance (MBR20L45CTG)	$R_{\theta JC}$	1.9	$^\circ\text{C}/\text{W}$
	$R_{\theta JA}$	45	
(MBRF20L45CTG)	$R_{\theta JC}$	2.2	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 10\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 10\text{ A}$, $T_C = 125^\circ\text{C}$) ($I_F = 20\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 20\text{ A}$, $T_C = 125^\circ\text{C}$)	V_F	0.50 0.47 0.63 0.62	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^\circ\text{C}$) (Rated DC Voltage, $T_C = 125^\circ\text{C}$)	i_R	0.5 170	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MBR20L45CTG, MBRF20L45CTG

TYPICAL CHARACTERISTICS

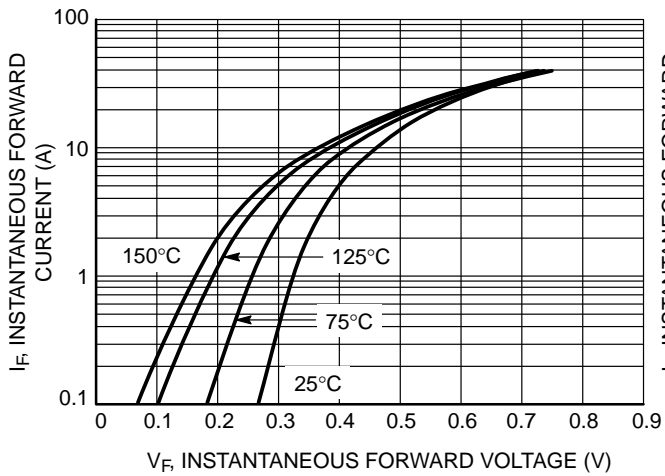


Figure 1. Typical Forward Voltage

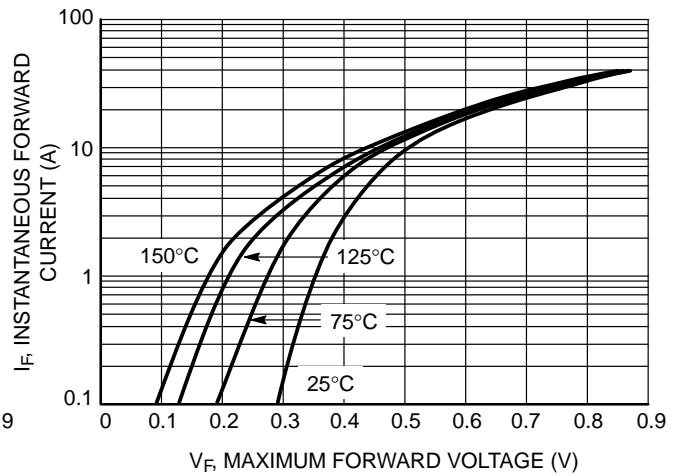


Figure 2. Maximum Forward Voltage

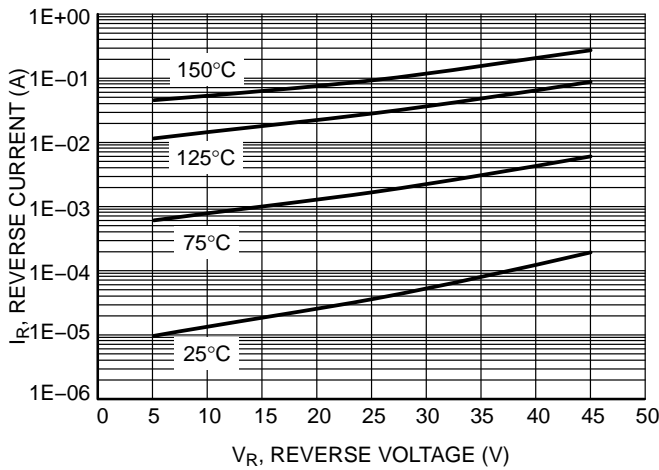


Figure 3. Typical Reverse Current

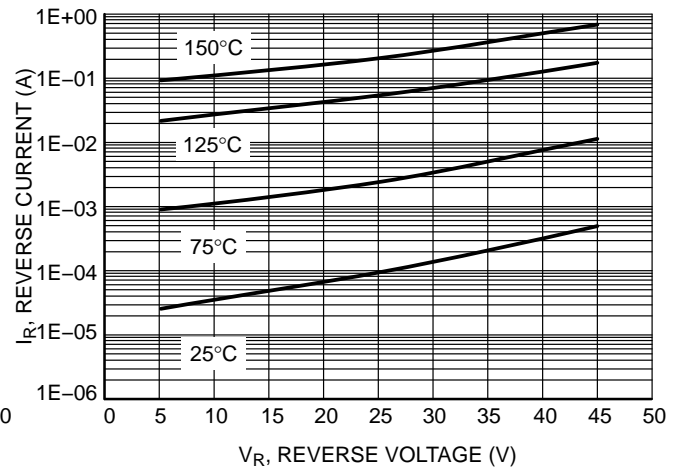


Figure 4. Maximum Reverse Current

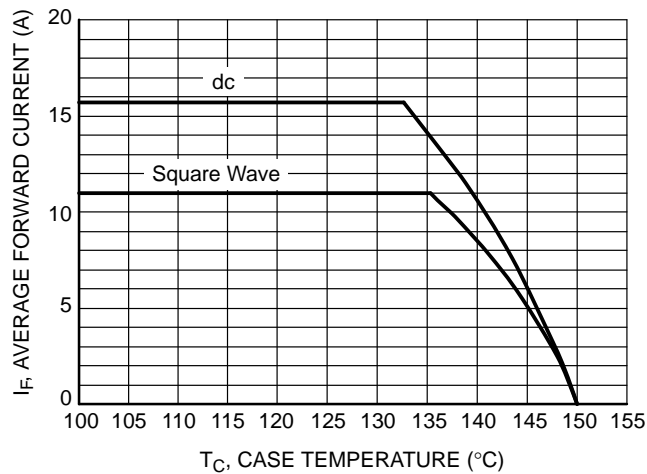


Figure 5. Current Derating

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TYPICAL CHARACTERISTICS

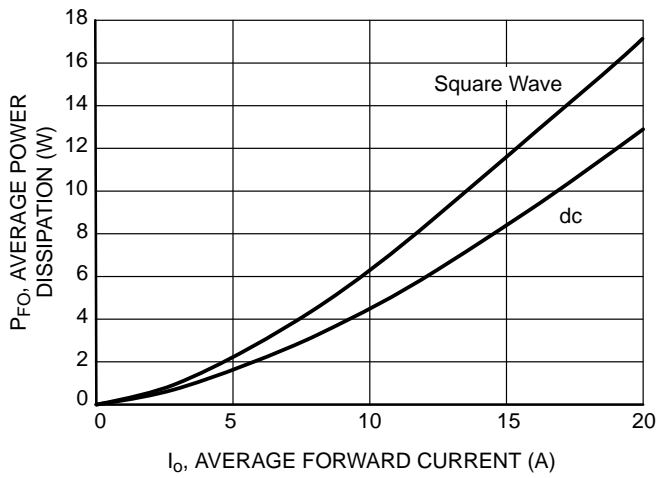


Figure 6. Forward Power Dissipation

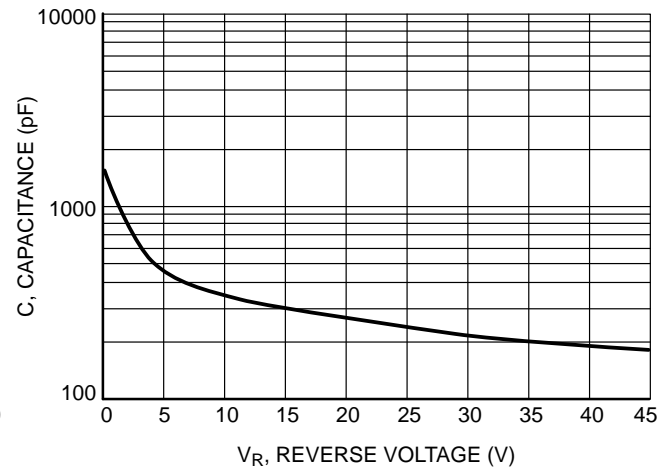


Figure 7. Typical Capacitance

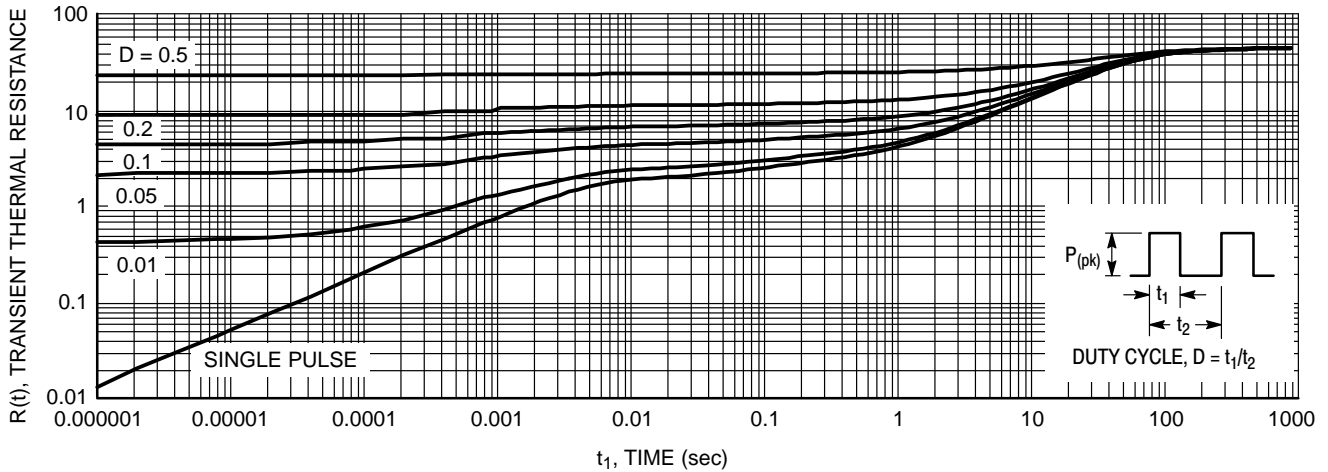


Figure 8. Thermal Response Junction-to-Ambient for MBR20L45CTG

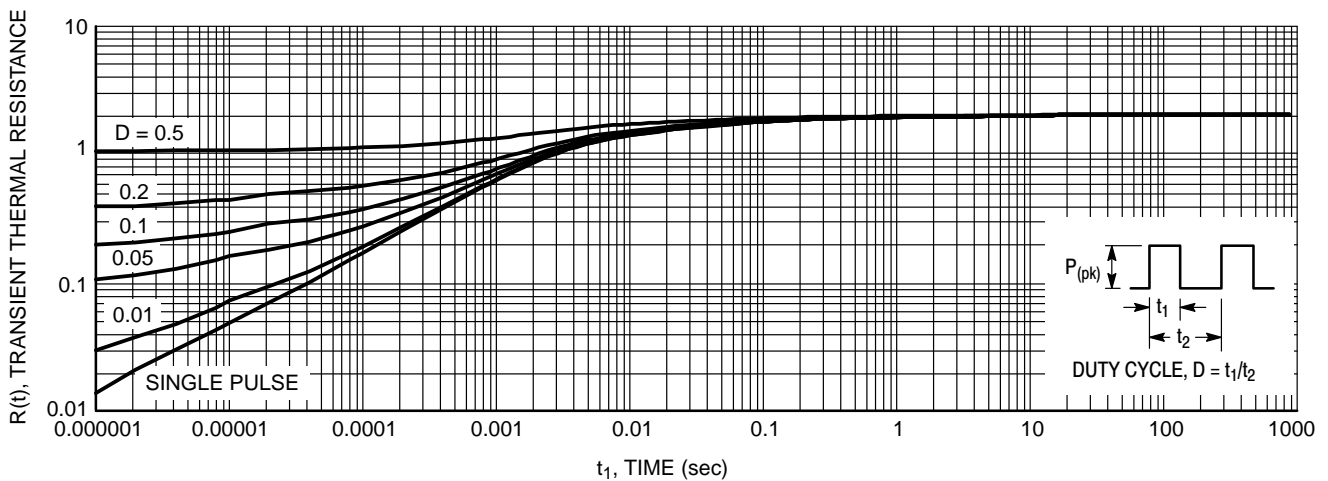


Figure 9. Thermal Response Junction-to-Case for MBR20L45CTG

MBR20L45CTG, MBRF20L45CTG

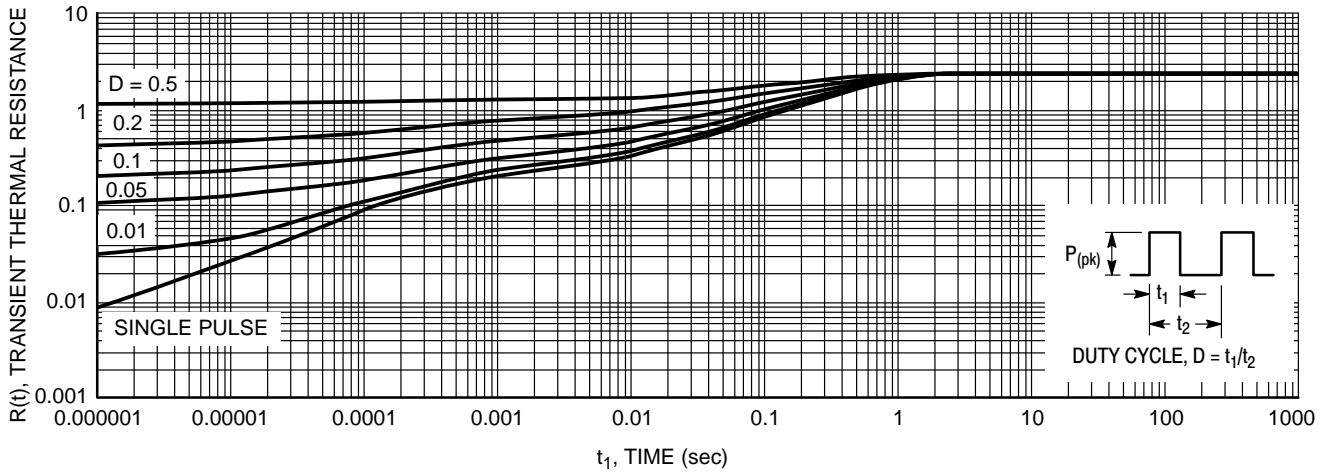
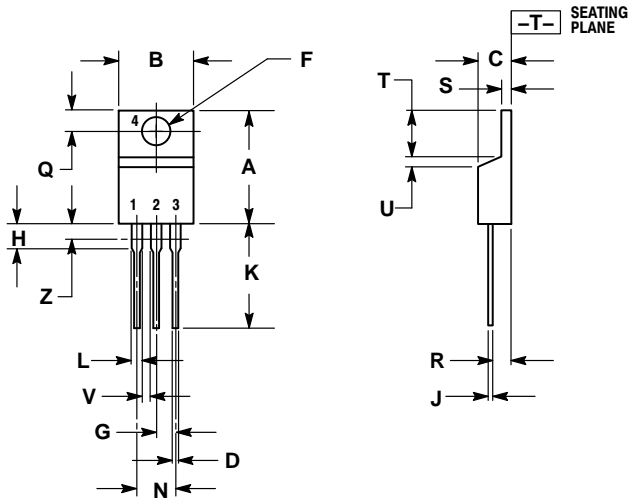


Figure 10. Thermal Response Junction-to-Case for MBRF20L45CTG

MBR20L45CTG, MBRF20L45CTG

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

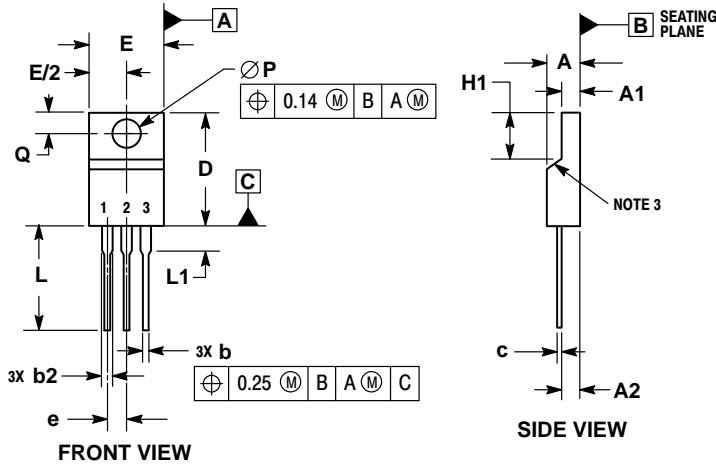
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.065	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

MBR20L45CTG, MBRF20L45CTG

PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD
CASE 221AH
ISSUE F




NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

MILLIMETERS		
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

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